

Group \blacklozenge	Material \blacklozenge	Symbol \blacklozenge	Band gap (eV) @ 302K \blacklozenge	Reference \blacklozenge
IV	Diamond	C	5.5	[6]
IV	Silicon	Si	1.11	[7]
IV	Germanium	Ge	0.67	[7]
III–V	Gallium(III) nitride	GaN	3.4	[7]
III–V	Gallium(III) phosphide	GaP	2.26	[7]
III–V	Gallium(III) arsenide	GaAs	1.43	[7]
IV–V	Silicon nitride	Si ₃ N ₄	5	
IV–VI	Lead(II) sulfide	PbS	0.37	[7]
IV–VI	Silicon dioxide	SiO ₂	9	
	Copper(I) oxide	Cu ₂ O	2.1	[8]

InSb=0.17eV

InAs=0.354eV

InP=1.344eV

Properties of major SiC polytypes^{[2][21]}

Polytype	3C (β)	4H	6H (α)
Crystal structure	Zinc blende (cubic)	Hexagonal	Hexagonal
Space group	T _d ² -F43m	C _{6v} ⁴ -P6 ₃ mc	C _{6v} ⁴ -P6 ₃ mc
Pearson symbol	cF8	hP8	hP12
Lattice constants (Å)	4.3596	3.0730; 10.053	3.0730; 15.11
Density (g/cm ³)	3.21	3.21	3.21
Bandgap (eV)	2.36	3.23	3.05
Bulk modulus (GPa)	250	220	220
Thermal conductivity (W cm ⁻¹ K ⁻¹) @ 300K (see [28] for temp. dependence)	3.6	3.7	4.9

